#### Nch 600V 46A Power MOSFET

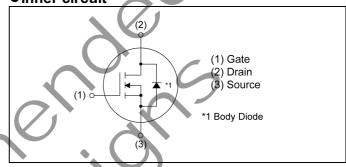
V <sub>DSS</sub>	600V
R <sub>DS(on)</sub> (Max.)	93mΩ
I <sub>D</sub>	±46A
P <sub>D</sub>	130W

# Outline TO-3PF

#### Features

- 1) Fast reverse recovery time (trr).
- 2) Low on-resistance.
- 3) Fast switching speed.
- 4) Gate-source voltage ( $V_{GSS}$ ) guaranteed to be  $\pm 30V$ .
- 5) Drive circuits can be simple.
- 6) Pb-free lead plating; RoHS compliant

#### •Inner circuit



Packaging specifications

or ackaging specimeations					
Paci	Packing	Tube			
0	Reel size (mm)	-			
	Tape width (mm)	-			
Туре	Basic ordering unit (pcs)	360			
	Taping code	C8			
	Marking	R6046FNZ			

# Application

Switching Power Supply

# ● Absolute maximum ratings (T<sub>a</sub> = 25°C ,unless otherwise specified)

Parameter	/1	Symbol	Value	Unit
Drain - Source voltage		V <sub>DSS</sub>	600	V
Continuo de decino cumo et	T <sub>C</sub> = 25°C	I <sub>D</sub> *1	±46	А
Continuous drain current	T <sub>C</sub> = 100°C	I <sub>D</sub> *1	±21.3	А
Pulsed drain current		l <sub>DP</sub> *2	±115	А
Gate - Source voltage		$V_{GSS}$	±30	V
Avalanche current, single pulse		I <sub>AS</sub> *3	23	Α
Avalanche energy, single pulse		E <sub>AS</sub> *3	142	mJ
Avalanche energy, repetitive	E <sub>AR</sub> *4	10	mJ	
Power dissipation (T <sub>c</sub> = 25°C)		P <sub>D</sub>	130	W
Junction temperature		T <sub>j</sub>	150	°C
Operating junction and storage temper	T <sub>stg</sub>	-55 to +150	°C	
Reverse diode dv/dt		dv/dt	15	V/ns

# ● Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V, I_{D} = 46A$ $T_{j} = 125^{\circ}C$	50	V/ns

#### ●Thermal resistance

Parameter	Symbol	Min	Values Typ.	Max.	Unit
Thermal resistance, junction - case	R <sub>thJC</sub>		- -	0.96	°C/W
Thermal resistance, junction - ambient	R <sub>thJA</sub>	7	-	40	°C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>		-	265	°C

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol Conditions		Values		Unit	
r ai ai nietei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V$ , $I_D = 1mA$	600	-	-	V
Drain - Source avalanche breakdown voltage	V <sub>(BR)DS</sub>	$V_{GS} = 0V, I_D = 23A$	-	700	-	V
$\sim$		$V_{DS} = 600V, V_{GS} = 0V$				
Zero gate voltage drain current	J <sub>DSS</sub>	$T_j = 25^{\circ}C$	-	-	0.1	mA
X	7	T <sub>j</sub> = 125°C	-	-	100	
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	3	-	5	V
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 23A				
Static drain - source on - state resistance	R <sub>DS(on)</sub> *6	T <sub>j</sub> = 25°C	-	75	93	mΩ
on state regionality		T <sub>j</sub> = 125°C	-	160	-	
Gate resistance	$R_{G}$	f = 1MHz, open drain	-	1.8	-	Ω

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Cymah ol	Symbol Conditions		Values		Lloit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward Transfer Admittance	Y <sub>fs</sub>  *6	V <sub>DS</sub> = 10V, I <sub>D</sub> = 23A	21	35	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	ı	6100		•
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 25V	-	3600		pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	90	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	V <sub>GS</sub> = 0V,		175	-	5 F
Effective output capacitance, time related	C <sub>o(tr)</sub>	V <sub>DS</sub> = 0V to 480V		596	-	pF
Turn - on delay time	t <sub>d(on)</sub> *6	$V_{DD} \simeq 300V$ , $V_{GS} = 10V$	- (	(17)	-	
Rise time	t <sub>r</sub> *6	I <sub>D</sub> = 23A	+	150	-	
Turn - off delay time	t <sub>d(off)</sub> *6	R <sub>L</sub> ≃ 13Ω	1	230	460	ns
Fall time	t <sub>f</sub> *6	$R_G = 10\Omega$	<b>7</b> )	80	160	

# ● Gate charge characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{*6}$	$V_{DD} \simeq 300V$	-	150	-	
Gate - Source charge	Q <sub>gs</sub> *6	I <sub>D</sub> = 46A	-	40	-	nC
Gate - Drain charge	$Q_{gd}^{*6}$	V <sub>GS</sub> = 10V	•	60	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} \simeq 300V$ , $I_D = 46A$	-	7.1	-	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*2</sup> Pw ≤ 10μs, Duty cycle ≤ 1%

<sup>\*3</sup> L  $\simeq$  500 $\mu$ H, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 $\Omega$ , starting T<sub>j</sub> = 25°C

<sup>\*4</sup> L  $\simeq$  500 $\mu$ H, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 $\Omega$ , starting T<sub>j</sub> = 25°C, f = 10kHz

<sup>\*5</sup> Reference measurement circuits Fig.5-1.

<sup>\*6</sup> Pulsed

# ● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Darameter	Cymah al	Canditions	Values			l limit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous forward current	I <sub>S</sub> *1	T - 25°C	-	-	46	А
Pulse forward current	I <sub>SP</sub> *2	T <sub>C</sub> = 25°C	-	- 6	115	A
Forward voltage	V <sub>SD</sub> *6	$V_{GS} = 0V, I_{S} = 46A$	-	- ~	1.5	V
Reverse recovery time	t <sub>rr</sub> *6		-	154	-	ns
Reverse recovery charge	Q <sub>rr</sub> *6	I <sub>S</sub> = 46A   di/dt = 100A/µs		0.74	-	μC
Peak reverse recovery current	I <sub>rrm</sub> *6	- αι/αι – 100/4μ3	V	9.6	-	Α
Peak rate of fall of reverse recovery current	di <sub>rr</sub> /dt	T <sub>j</sub> = 25°C	):	1200	-	A/µs

### Typical transient thermal characteristics

Symbol	Value	Unit
R <sub>th1</sub>	0.0341	
R <sub>th2</sub>	0.266	k/W
R <sub>th3</sub>	1.24	•

Symbol	Value	Unit
O <sub>th1</sub>	0.0112	
C <sub>th2</sub>	0.133	Ws/K
C <sub>th3</sub>	1.27	

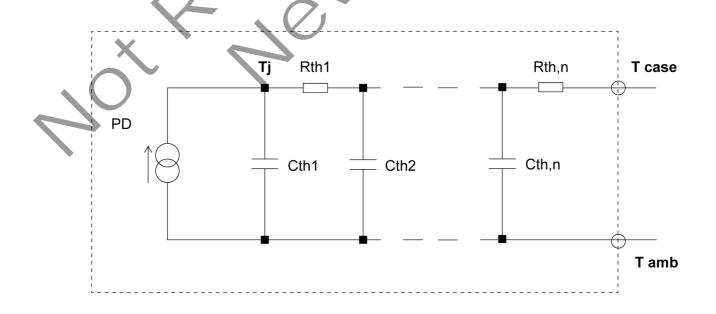


Fig.1 Power Dissipation Derating Curve

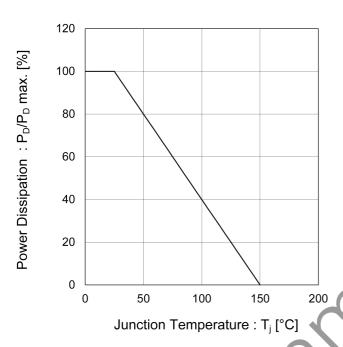


Fig.2 Maximum Safe Operating Area

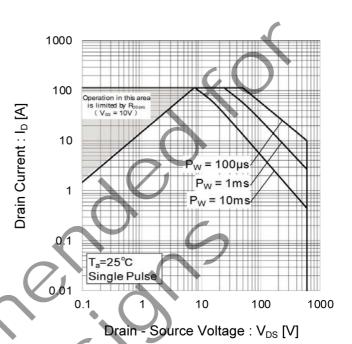
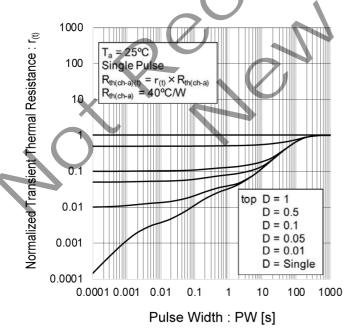


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



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Fig.4 Avalanche Current vs. Inductive Load

Fig.5 Avalanche Power Losses

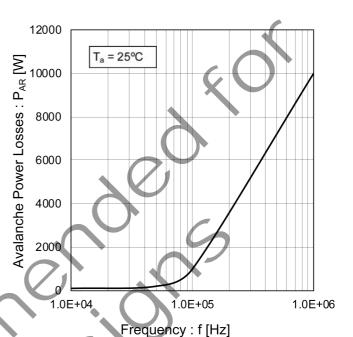


Fig.6 Avalanche Energy Derating Curve vs. Junction Temperature

Coil Inductance : L [mH]

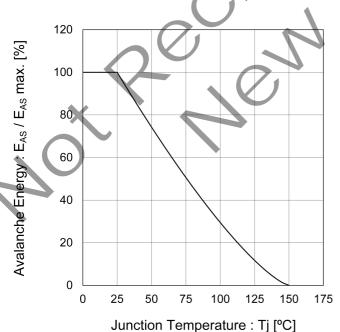
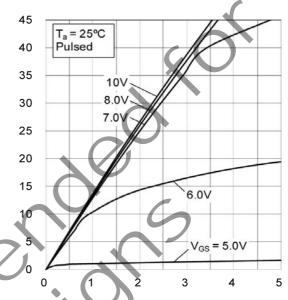


Fig.7 Typical Output Characteristics(I)

45 6.5V  $T_a = 25^{\circ}C$ 40 Pulsed 35 8.0V Drain Current : I<sub>D</sub> [A] 30 7.0V 25 6.0V 20 15 10 5  $V_{GS} = 5.0V$ 0 0 10 20 30 40

Fig.8 Typical Output Characteristics(II)

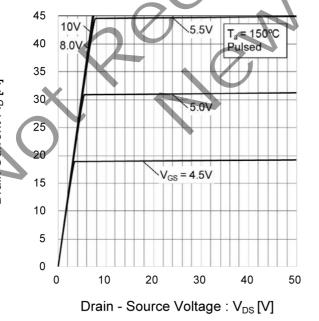


Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.10 Tj = 150°C Typical Output

Characteristics (II)

Fig.9 Tj = 150°C Typical Output Characteristics (I)



Drain Current : I<sub>D</sub> [A]

Drain Current : I<sub>D</sub> [A]

45 T<sub>a</sub> = 150°C 40 Pulsed 35 10V 30 6.0V 25 5.0V 20  $V_{GS} = 4.5V$ 15 10 5 0 2 0 3 5 Drain - Source Voltage: V<sub>DS</sub>[V]

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Fig.11 Breakdown Voltage vs. Junction Temperature

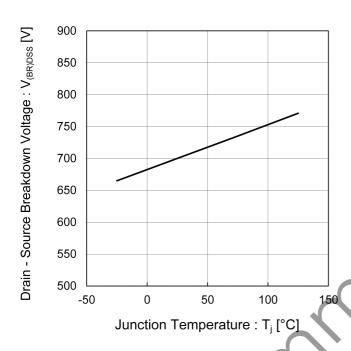


Fig.12 Typical Transfer Characteristics

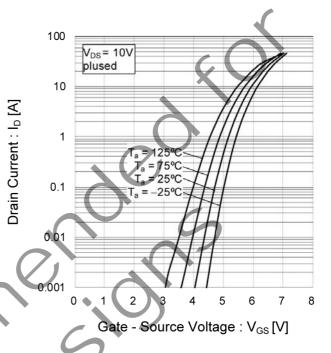


Fig.13 Gate Threshold Voltage vs. Junction Temperature

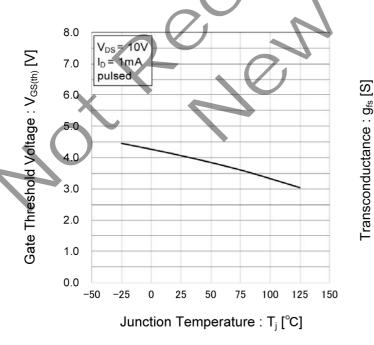


Fig.14 Transconductance vs. Drain Current

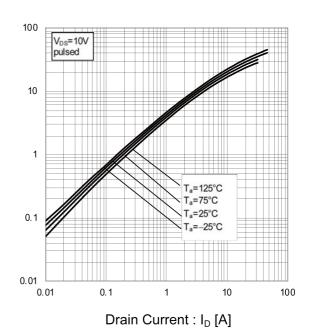


Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

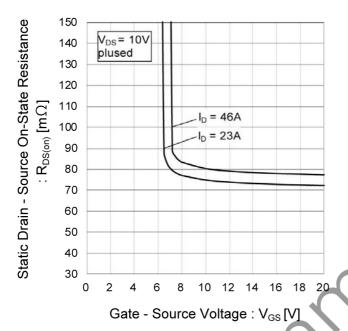


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature

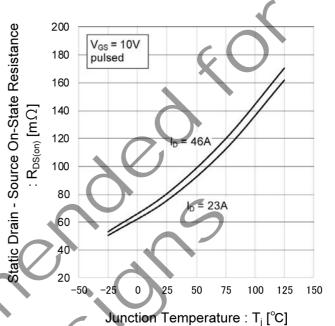
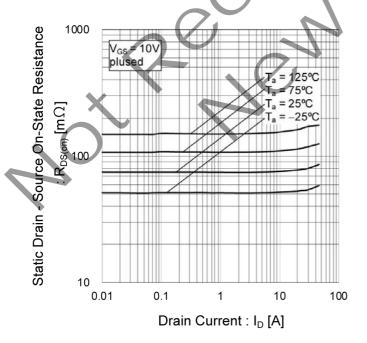
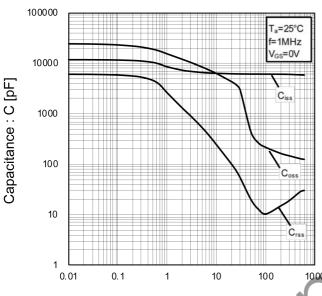


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current



9/13

Fig.18 Typical Capacitance vs. Drain - Source Voltage



Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.19 Coss Stored Energy

Coss Stored Energy : E $_{
m oss}$  [  $\mu$  J

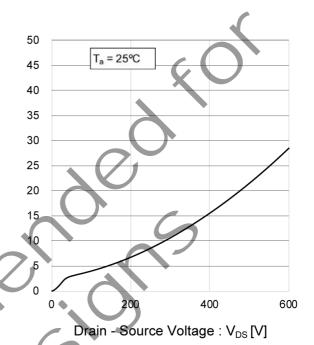


Fig.20 Switching Characteristics

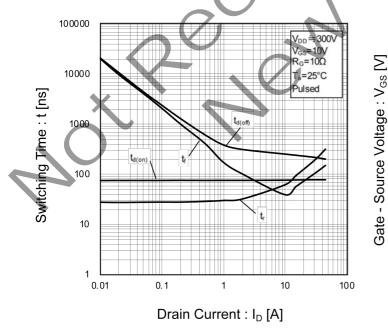


Fig.21 Dynamic Input Characteristics

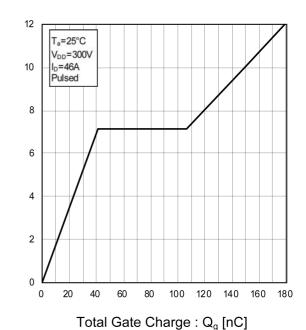


Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

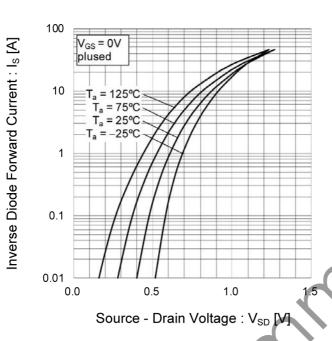
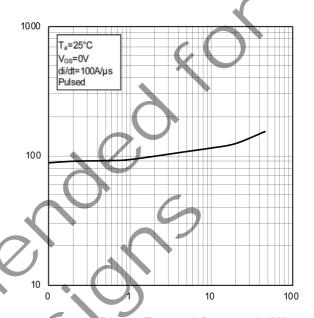


Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



Inverse Diode Forward Current : I<sub>S</sub> [A]

Reverse Recovery Time : t<sub>rr</sub> [ns]

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#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

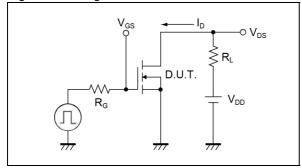


Fig.2-1 Gate Charge Measurement Circuit

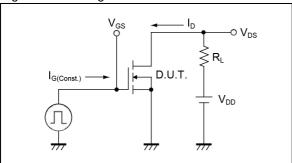


Fig.3-1 Avalanche Measurement Circuit

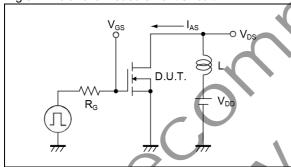


Fig.4-1 dv/dt Measurement Circuit

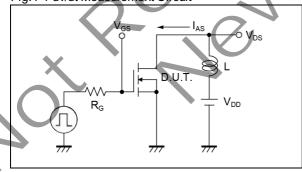


Fig.5-1 di/dt Measurement Circuit

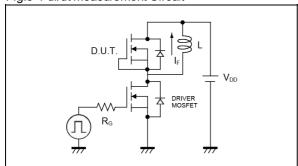


Fig.1-2 Switching Waveforms

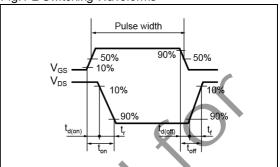


Fig.2-2 Gate Charge Waveform

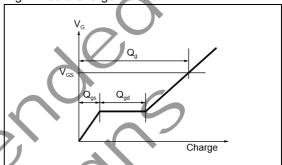


Fig.3-2 Avalanche Waveform

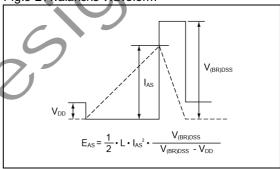


Fig.4-2 dv/dt Waveform

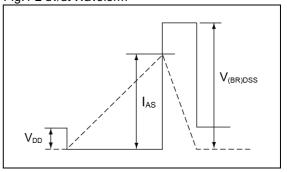
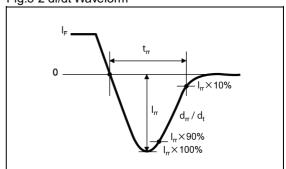
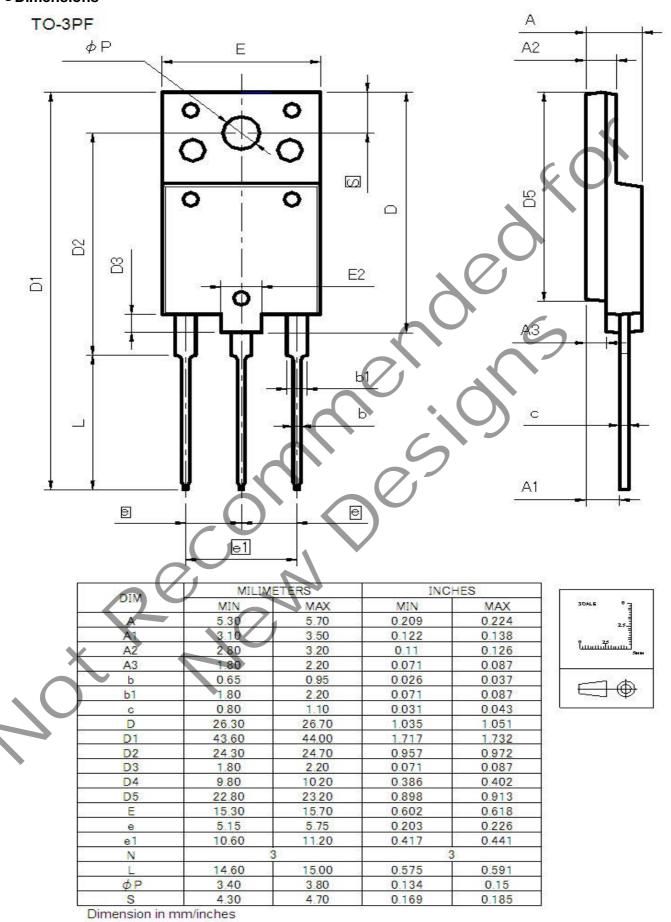


Fig.5-2 di/dt Waveform



#### Dimensions



# **Notice**

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JÁPAN	USA	EU	CHINA
CLASSⅢ	CL A C C TT	CLASS II b	CLASSⅢ
CLASSIV	CLASSⅢ	CLASSⅢ	CLASSIII

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  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
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  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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